MMBF170
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Please click here to visit our online spice models database.

## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)


## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

SOT-23


Equivalent Circuit


TOP VIEW

Maximum Ratings $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic |  | Symbol | Value | Units |
| :---: | :---: | :---: | :---: | :---: |
| Drain-Source Voltage |  | $V_{\text {DSS }}$ | 60 | V |
| Drain-Gate Voltage $\mathrm{R}_{\mathrm{GS}} \leq 1.0 \mathrm{M} \Omega$ |  | V DGR | 60 | V |
| Gate-Source Voltage | Continuous Pulsed | VGSS | $\begin{aligned} & \pm 20 \\ & \pm 40 \end{aligned}$ | V |
| Drain Current (Note 1) | Continuous Pulsed | ID | $\begin{aligned} & 500 \\ & 800 \end{aligned}$ | mA |

Thermal Characteristics $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Value |  |
| :--- | :---: | :---: | :---: |
| Total Power Dissipation (Note 1) | $\mathrm{P}_{\mathrm{d}}$ | 300 | Units |
| Thermal Resistance, Junction to Ambient | $\mathrm{R}_{\theta \mathrm{JA}}$ | 1.80 | mW |
| Operating and Storage Temperature Range | $\mathrm{T}_{\mathrm{j},}, \mathrm{T}_{\mathrm{STG}}$ | -517 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |

Electrical Characteristics
$@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS (Note 3) |  |  |  |  |  |  |
| Drain-Source Breakdown Voltage | BV ${ }_{\text {DSS }}$ | 60 | 70 | - | V | $\mathrm{V}_{G S}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=100 \mu \mathrm{~A}$ |
| Zero Gate Voltage Drain Current | IDSS | - | - | 1.0 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{DS}}=60 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ |
| Gate-Body Leakage | IGSs | - | - | $\pm 10$ | nA | $\mathrm{V}_{\mathrm{GS}}= \pm 15 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |
| ON CHARACTERISTICS (Note 3) |  |  |  |  |  |  |
| Gate Threshold Voltage | $\mathrm{V}_{\mathrm{GS}}(\mathrm{th})$ | 0.8 | 2.1 | 3.0 | V | $V_{D S}=V_{G S}, I_{D}=250 \mu \mathrm{~A}$ |
| Static Drain-Source On-Resistance | RDS (on) | - | - | $\begin{aligned} & \hline 5.0 \\ & 5.3 \end{aligned}$ | $\Omega$ | $\begin{aligned} & \mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=200 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{GS}}=4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=50 \mathrm{~mA} \end{aligned}$ |
| Forward Transconductance | gFs | 80 | - | - | mS | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=0.2 \mathrm{~A}$ |
| DYNAMIC CHARACTERISTICS |  |  |  |  |  |  |
| Input Capacitance | Ciss | - | 22 | 40 | pF | $V_{\text {DS }}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{f}=1.0 \mathrm{MHz}$ |
| Output Capacitance | Coss | - | 11 | 30 | pF |  |
| Reverse Transfer Capacitance | $\mathrm{C}_{\text {rss }}$ | - | 2.0 | 5.0 | pF |  |
| SWITCHING CHARACTERISTICS |  |  |  |  |  |  |
| Turn-On Time | $\mathrm{t}_{\text {on }}$ | - | - | 10 | ns | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=25 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=0.5 \mathrm{~A}, \\ & \mathrm{~V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=50 \Omega \end{aligned}$ |
| Turn-Off Time | $\mathrm{t}_{\text {off }}$ | - | - | 10 | ns |  |

Notes: 1. Device mounted on FR-4 PCB $1.0 \times 0.75 \times 0.062$ inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
No purposefully added lead. Halogen and Antimony Free.
. Short duration pulse test used to minimize self-heating effect.
Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or $\mathrm{Sb}_{2} \mathrm{O}_{3}$ Fire Retardants.


Fig． 1 On－Region Characteristics


Fig． 3 On－Resistance vs．Junction Temperature


Fig． 5 Max Power Dissipation vs．Ambient Temperature


Fig． 2 On－Resistance vs．Drain Current


Fig． 4 On－Resistance vs．Gate－Source Voltage

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MMBF170

## Ordering Information（Note 5）

| Part Number | Case | Packaging |
| :---: | :---: | :---: |
| MMBF170－7－F | SOT－23 | $3000 /$ Tape \＆Reel |

Notes：$\quad$ 5．For packaging details，go to our website at http：／／www．diodes．com／datasheets／ap02007．pdf．

## Marking Information

| Z＝Product Type Marking Code <br> ＝Date Code Marking <br> $=$ Year ex：$N=2002$ <br> $=$ Month ex： 9 ＝September |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Date Code Key |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |
| Year | 1998 | 1999 | 2000 | 2001 | 2002 | 2003 | 200 |  | 200 |  |  | 2008 | 2009 | 2010 | 2011 | 2012 |
| Code | J | K | L | M | N | P | R |  | S |  |  | V | W | X | Y | Z |
| Month | Jan | Feb | Mar |  | Apr | May | Jun |  |  | Jul |  | Sep | Oct | Nov |  | Dec |
| Code | 1 | 2 | 3 |  | 4 | 5 | 6 |  |  | 7 |  | 9 | 0 | N |  | D |

## Package Outline Dimensions



## Suggested Pad Layout



| Dimensions | Value（in mm） |
| :---: | :---: |
| Z | 3.4 |
| G | 0.7 |
| X | 0.9 |
| Y | 1.4 |
| C | 2.0 |
| E | 0.9 |

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